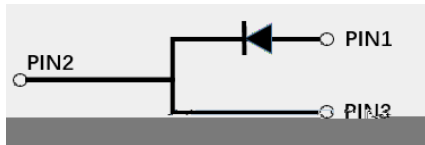
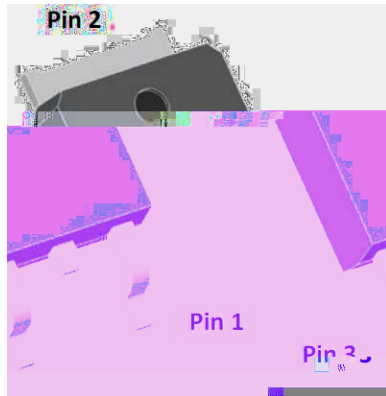


V_{RRM}	650V
I_F 135°C	14A
Q_C	30nC



Positive temperature coefficient
 Temperature-independent switching
 Maximum working temperature at 175 °C
 Unipolar devices and zero reverse recovery current
 Zero forward recovery current
 Essentially no switching losses
 Reduction of heat sink requirements
 AEC-Q101 qualified
 High-frequency operation
 Reduction of EMI

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, automotive battery chargers.

: TO-252

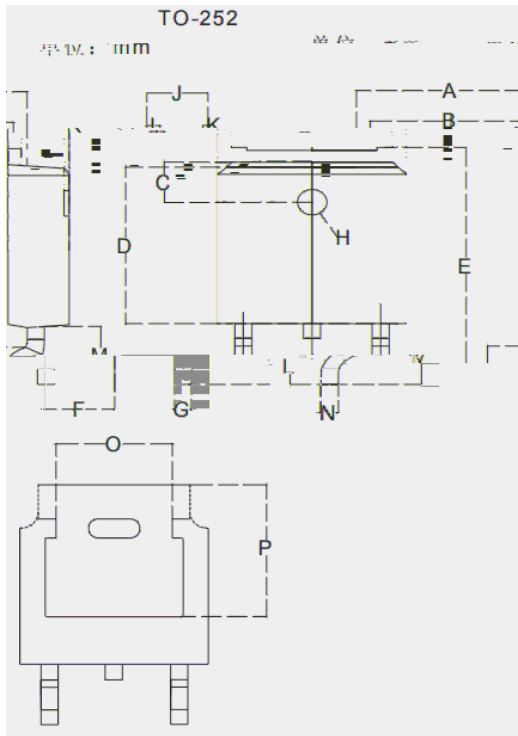
Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant, halogen-free

: Tin plated leads

: As marked

($T_C=25$ Unless otherwise specified)

Device marking code			D106510DQG2
Reverse voltage (repetitive peak) @ $T_j=25^\circ\text{C}$	V_{RRM}	V	650
Reverse voltage (Surge Peak) @ $T_j=25^\circ\text{C}$	V_{RSM}	V	650
Reverse voltage (DC) @ $T_j=25^\circ\text{C}$	V_{DC}	V	650
Continuous forward current @ $T_c=25^\circ\text{C}$	I_F	A	32
Continuous forward current @ $T_c=135^\circ\text{C}$			14
Continuous forward current @ $T_c=154^\circ\text{C}$			10
Non-repetitive peak forward surge current @ $T_c=25^\circ\text{C}$, $t_p=10\text{ms}$, Half Sine Wave	I_{FSM}	A	70
Power Dissipation @ $T_c=25^\circ\text{C}$	P_{TOT}	W	132
Power Dissipation @ $T_c=110^\circ\text{C}$			57
i^2t Value @ $T_c=25^\circ\text{C}$, $t_p=10\text{ms}$	i^2dt	A^2S	32
Operating junction and Storage temperature range	T_j, T_{slg}	$^\circ\text{C}$	-55 to +175



TO-252		
Dim	Min	Max
A	6.500	6.700
B	5.100	5.460
C	1.400	1.800
D	6.200	6.000
E	10.400	10.000
F	2.366	2.166
G	0.860	0.660
H	$\Phi 1.050$	$\Phi 1.350$
I	0.460	0.580
J	2.200	2.400
K	0	0.300
L	0.890	2.290
M	2.700	2.380
N	0.580	0.430
O	0.95	4.20
P	4.6	4.1



The information presented in this document is for reference only. Yangzhou Yangjie Electronic Technology Co., Ltd. reserves the right to make changes without notice for the specification of the products displayed herein to improve reliability, function or design or otherwise.

H

f